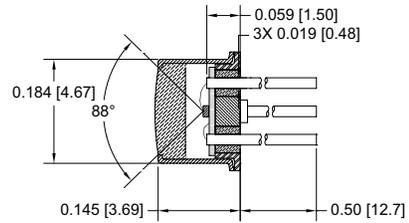
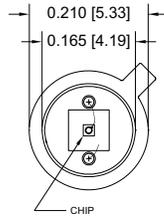
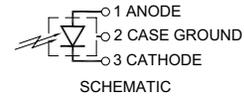
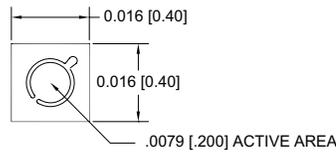




PACKAGE DIMENSIONS INCH [mm]



CHIP DIMENSIONS INCH [mm]



TO-46 PACKAGE

FEATURES

- Low noise
- Low dark current
- High response

DESCRIPTION

The **SD 008-11-41-211** is a high sensitivity low noise characteristics InGaAs photodiode packaged in a leaded hermetic TO-46 metal package.

APPLICATIONS

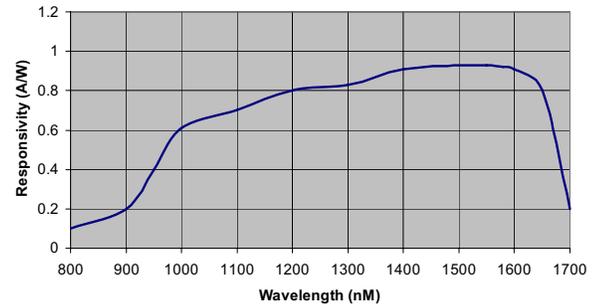
- Communication
- Industrial
- Medical

ABSOLUTE MAXIMUM RATING (TA)= 23°C UNLESS OTHERWISE NOTED

SYMBOL	PARAMETER	MIN	MAX	UNITS
V _{BR}	Reverse Voltage		75	V
T _{STG}	Storage Temperature	-55	+100	°C
T _O	Operating Temperature	-40	+85	°C
T _S	Soldering Temperature*		+260	°C

* 1/16 inch from case for 3 seconds max.

SPECTRAL RESPONSE



ELECTRO-OPTICAL CHARACTERISTICS RATING (TA)= 23°C UNLESS OTHERWISE NOTED

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I _D	Dark Current	V _R = 5V		1	5.0	nA
R _{SH}	Shunt Resistance	V _R = 10 mV	100	300		MΩ
C _J	Junction Capacitance	V _R = 5V, f = 1 MHz		9	10	pF
λ _{range}	Spectral Application Range	Spot Scan	800		1700	nm
R	Responsivity	λ = 1310nm, V _R = 5V	0.83	0.92		A/W
V _{BR}	Breakdown Voltage	I = 1μA		10		V
NEP	Noise Equivalent Power	V _R = 5V @ λ = 1310nm		1.79X10 ⁻¹⁴		W/√Hz
t _r	Response Time**	RL = 50 Ω, V _R = 5V			0.23	nS

**Response time of 10% to 90% is specified at 1310nm wavelength light.

Information in this technical datasheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice.